

Please amend the "Abstract" on page 34 as follows:

ABSTRACT OF THE DISCLOSURE

The invention includes a magnetoresistive memory device having a conductive core, and a first magnetic layer extending at least partially around the conductive core. A non-magnetic material is over at least a portion of the first magnetic layer and separated from the conductive core by at least the first magnetic layer. A second magnetic layer is over the non-magnetic material, and separated from the first magnetic layer by at least the non-magnetic material. The invention also includes methods of forming magnetoresistive memory devices. The invention includes a method of forming a magnetoresistive memory device. A trench is formed in an insulative material, and the trench is partially filled with a first magnetic material to narrow the trench. The narrowed trench is at least partially filled with a conductive material. A second magnetic material is formed over the conductive material. A non-magnetic layer is formed over the second magnetic material. A third magnetic material is formed over the non-magnetic layer. The conductive material and the first and second magnetic materials are incorporated into a sense portion of the magnetoresistive memory device. The third magnetic material is incorporated into a reference portion of the magnetoresistive memory device.